

TOSHIBA

2SK2745

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOSV)

2SK2745

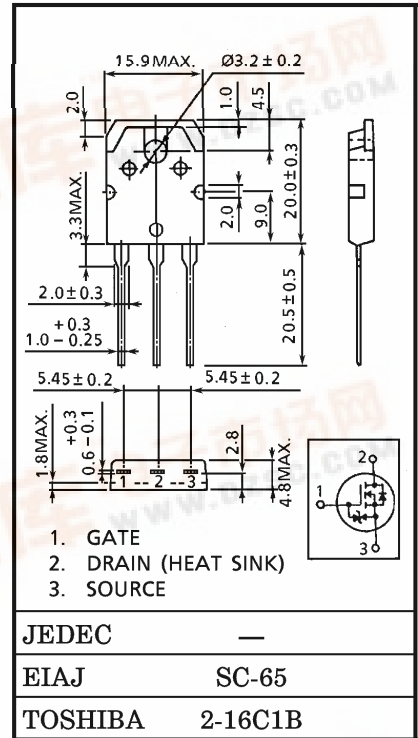
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
 Unit in mm

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 7.0m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 50S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 50V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	50	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	50 A
	Pulse	I_{DP}	200 A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	150	W
Single Pulse Avalanche Energy**	E_{AS}	747	mJ
Avalanche Current	I_{AR}	50	A
Repetitive Avalanche Energy*	E_{AR}	15	mJ
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 4.6g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	°C/W
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	°C/W

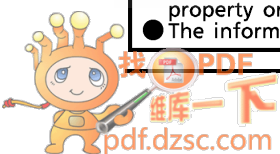
Note ;

- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- ** $V_{DD} = 25V$, Starting $T_{ch} = 25^\circ C$, $L = 368\mu H$, $R_G = 25\Omega$, $I_{AR} = 50A$

This transistor is an electrostatic sensitive device. Please handle with caution.

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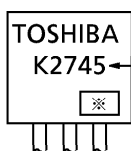
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 50V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	50	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4V, I_D = 25A$	—	11	16	m Ω
			$V_{GS} = 10V, I_D = 25A$	—	7	9.5	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 25A$	30	50	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	—	4000	—	pF
Reverse Transfer Capacitance		C_{rss}		—	800	—	
Output Capacitance		C_{oss}		—	2000	—	
Switching Time	Rise Time	t_r	<p>$I_D = 25A$ $V_{GS} = 10V, 0V$ $R_L = 1.0\Omega$ $V_{DD} \doteq 25V$</p>	—	25	—	ns
	Turn-on Time	t_{on}		—	40	—	
	Fall Time	t_f		—	120	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_w = 10\mu s$	—	360	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 40V, V_{GS} = 10V$ $I_D = 50A$	—	130	—	nC
Gate-Source Charge		Q_{gs}		—	90	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	40	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	50	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	200	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 50A, V_{GS} = 0V$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 50A, V_{GS} = 0V$	—	140	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	80	—	nC

MARKING

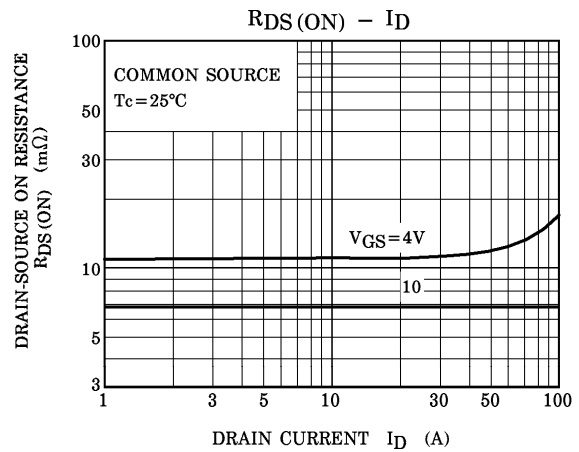
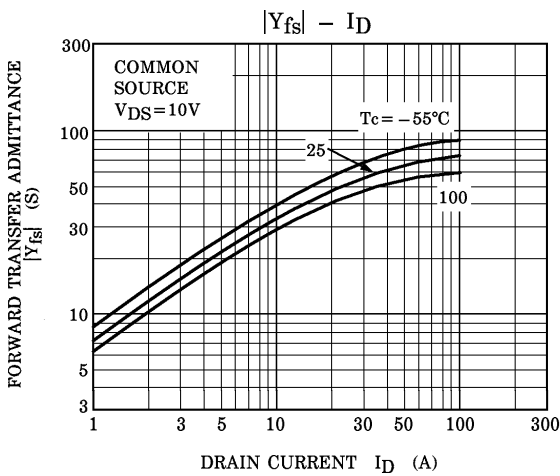
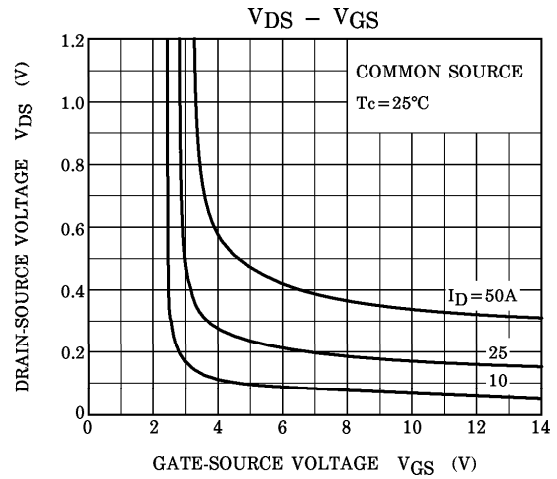
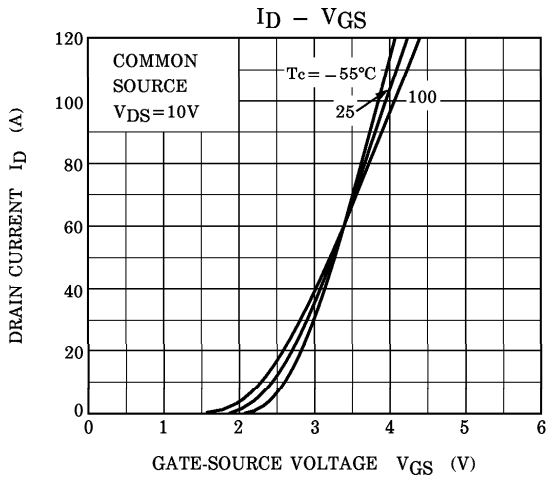
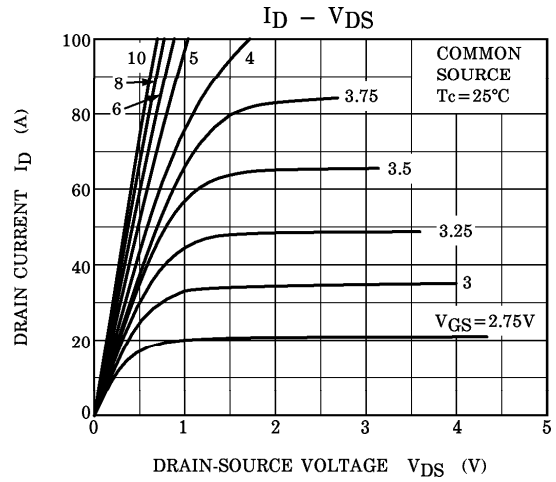
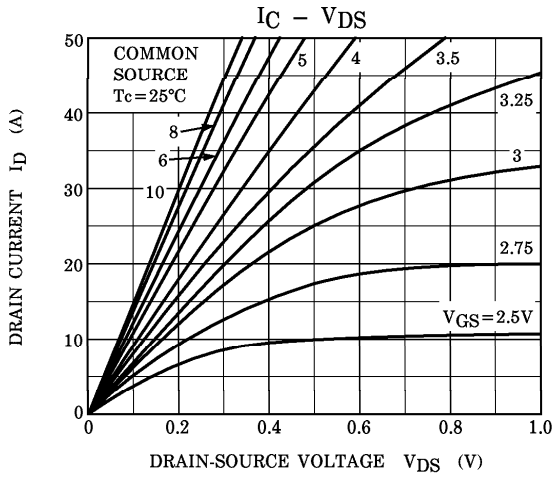


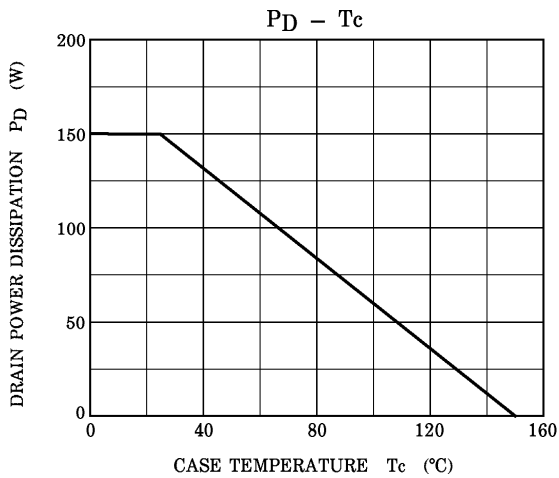
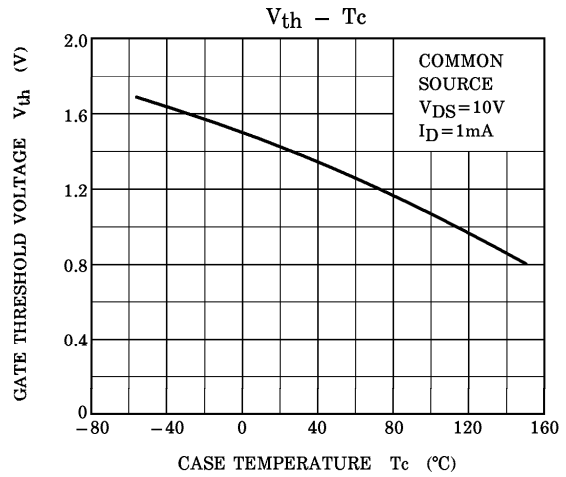
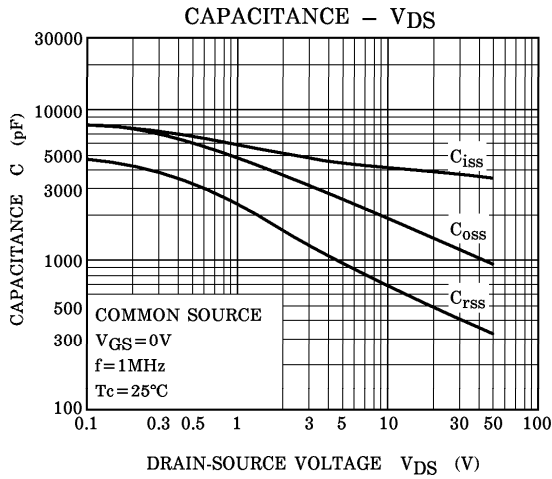
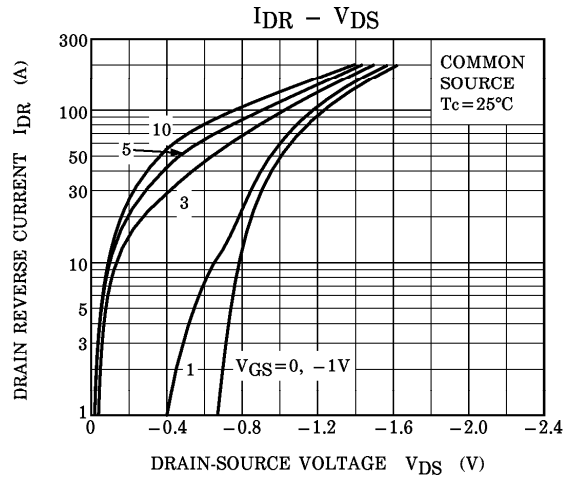
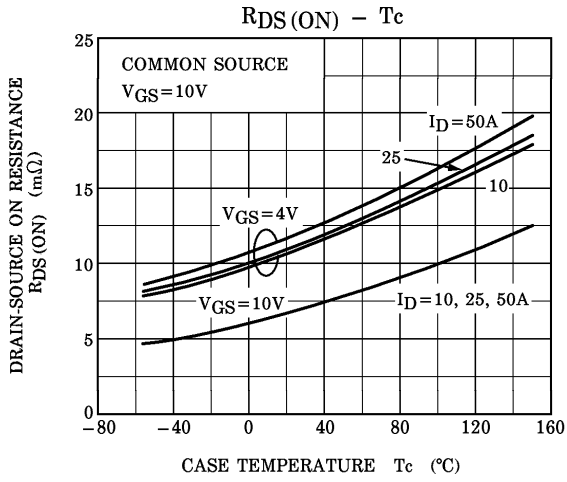
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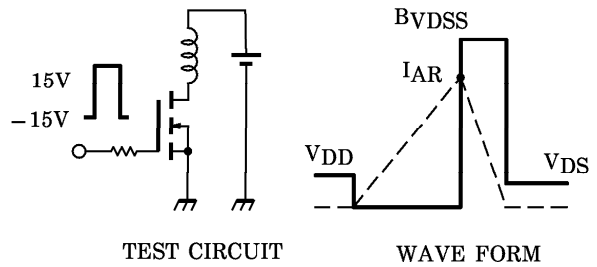
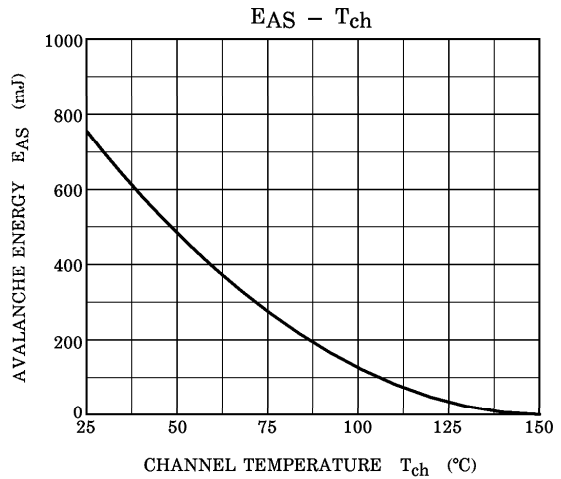
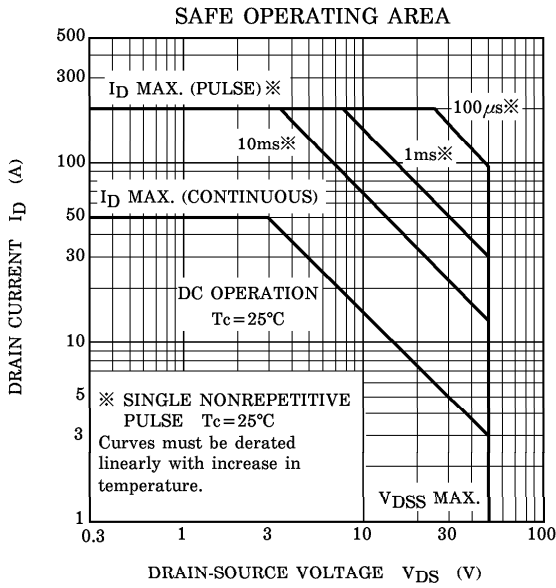
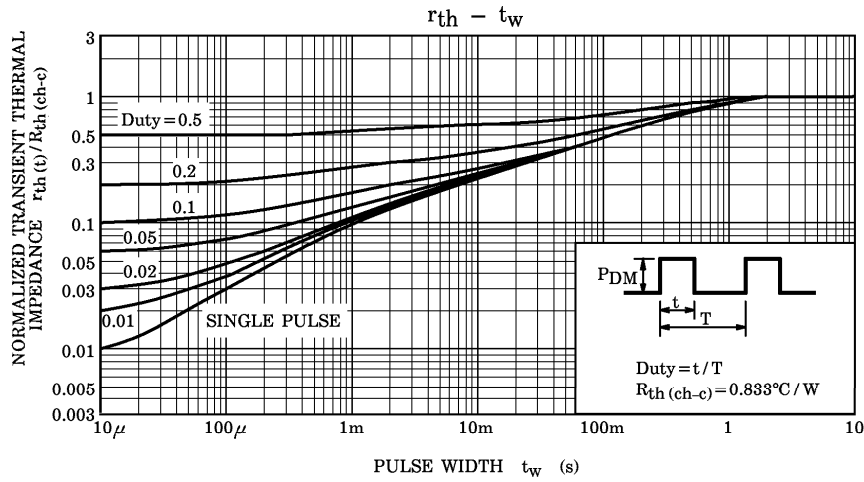
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 50A$, $R_G = 25\Omega$
 $V_{DD} = 25V$, $L = 368\mu H$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$